Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A method of manufacturing a Metal Oxide Semiconductor (MOS) transistor, comprising:

forming an active area in a substrate, wherein said active area is bounded by an isolation structure; and

placing at least one stress adjustor adjacent said active area, wherein said stress adjustor is positioned to modify a mobility of a majority carrier within a channel region of said MOS transistor, wherein placing said stress adjustor includes removing portions of said silicon substrate to form at least two trenches, wherein a portion of said silicon substrate remaining between said at least two trenches forms said stress adjustor and filling said trenches with a material comprising said isolation structure, wherein said stress adjustor and a first of said at least two trenches are located between a portion of a second of said at least two trenches and said active area.

2. (cancelled)

3. (currently amended) A method of manufacturing a Metal Oxide Semiconductor (MOS) transistor, comprising:

forming an active area in a substrate, wherein said active area is bounded by an isolation structure; and

placing at least one stress adjustor adjacent said active area, wherein said stress adjustor is positioned to modify a mobility of a majority carrier within a channel region of said MOS transistor, ~~The method as recited in Claim 1,~~ wherein placing said stress

adjustor includes removing a portion of said isolation structure to form a trench and filling said trench with an insulator.

4. (original) The method as recited in Claim 3, wherein filling said trench with said insulator includes a high density plasma oxide deposition.

5. (original) The method as recited in Claim 3, wherein filling said trench with said insulator includes a spin-on-glass type oxide.

6. (original) The method as recited in Claim 1, wherein said stress adjustor is configured to decrease a compressive stress imparted from said isolation structure to said channel region.

7. (withdrawn) The method as recited in Claim 1, wherein said stress adjustor is configured to increase a compressive stress imparted from said isolation structure to said channel region.

Cancel Claims 6-20.